

Monolithic Amplifier

TSS-23LN+

Mini-Circuits

50Ω 30 MHz to 2 GHz

THE BIG DEAL

- High IP3, +36.4 dBm typ. at 1GHz
- Gain, 21.5 dB typ. at 1 GHz
- Low noise figure, 1.2 dB at 1 GHz
- Low voltage, +5V and +3V
- Shutdown feature



Generic photo used for illustration purposes only

CASE STYLE: DQ1225

+ROHS Compliant The +Suffix identifies RoHS Compliance. See our website for methodologies and qualifications

APPLICATIONS

- Base station infrastructure
- CATV
- Cellular

PRODUCT OVERVIEW

TSS-23LN+ (RoHS compliant) is an advanced wideband amplifier with shutdown feature. It is fabricated using E-PHEMT technology and offers extremely high dynamic range over a broad frequency range and with low noise figure. In addition, the TSS-23LN+ has good input and output return loss over a broad frequency range. TSS-23LN+ is enclosed in a 3mm x 3mm, 12-lead MCLP package and has very good thermal performance.

KEY FEATURES

| Feature | Advantages |
|---|---|
| Broad Band: 30MHz to 2GHz | Broadband covering primary wireless communications bands: VHF, UHF, Cellular |
| Extremely High IP3 +39.8 dBm typical at 30 MHz +36.4 dBm typical at 1 GHz | The TSS-23LN+ matches industry leading IP3 performance relative to device size and power consumption. The combination of the design and E-PHEMT Structure provides enhanced linearity over a broad frequency range as evidence in the IP3 being approximately 11-17 dB above the P1dB point. This feature makes this amplifier ideal for use in: • Driver amplifiers for complex waveform up converter paths • Drivers in linearized transmit systems • Secondary amplifiers in ultra-High Dynamic range receivers |
| Shutdown feature | Allow users to turn on and off the amplifier with pulsed signals while keeping the power supply at constant voltage to minimize DC power consumption |
| Low Noise Figure, 1.2 dB at 1 GHz | Enables lower system noise figure performance and along with High OIP3 provides high dynamic range |
| Low Supply Voltage | TSS-23LN+ supports low supply voltage operation which indicate low power consumption. |

REV. B ECO-022590 TSS-23LN+ MCL NY 240731



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ELECTRICAL SPECIFICATIONS¹ AT +25°C & 50Ω, UNLESS NOTED OTHERWISE Amplifier-Amplifier-Amplifier-Amplifier-ON ÓFF ΟN ÓFF Condition Parameter Units (MHz) VDD = +5V VDD = +5V VDD = +3V VDD = +3V Min. Max. Тур. Тур. Тур. Typ. Frequency Range 2000 30-2000 30-2000 30-2000 MHz 30 30 1.2 1.1 500 1.2 1.2 Noise Figure 1000 1.2 dB 1.2 1500 1.3 1.4 2000 1.5 1.4 30 20.7 23.1 25.3 -21 22.4 -21 500 22.2 -21 21.4 -21 Gain 1000 19.2 21.5 23.4 -23 20.2 -24 dB 1500 20.7 -26 19.1 -26 21.6 -28 -27 2000 17.6 19.9 18 **Reversed Isolation** 30-2000 27 26 27 25 dB 30 12 12 12 12 500 12 12 11 12 Input Return Loss 1000 10 12 8 12 dB 1500 10 15 8 15 2000 19 8 19 11 30 15 2 17 2 500 15 2 19 2 2 2 **Output Return Loss** 1000 16 18 dB 1500 12 2 11 2 2000 10 2 9 2 30 +22.8 +17.1 500 +23.8 +18.9 1000 Output Power @1dB compression AMP-ON +24.1dBm +19 1500 +23.5 +18.8 2000 +22.8 +18.1 30 +39.8 +34.1 500 +38.0 +33.7 _ Output IP3 (Pout = 0dBm/Tone) 1000 +36.4+31.8 dBm 1500 +33 +35.5 +31.1 2000 +34.0 +30.3 Device Operating Voltage (VDD) +4.75 +5 +5.25 +5 +3 +3 V 139 Device Operating Current (ID) 74 163 5 3 mΑ Control Voltage (VG) +5 0 +5 v 0 DC Current (ID) Variation Vs. Temperature² -13 27 uA/degC DC Current (ID) Variation Vs. Voltage 0.034 0.033 mA/mV Thermal Resistance 23.3 23.3 degC/W

1. Measured on Mini-Circuits Characterization test board TB-TSS-23LN+. See Characterization Test Circuit (Fig. 1)

2. (Current at 105°C - Current at -45°C)/150

ABSOLUTE MAXIMUM RATINGS³

| Ratings |
|---|
| -40°C to 105°C |
| -65°C to 150°C |
| 3.3W |
| +28 dBm (5 minutes max.) +10 dBm (continuos) for 0.03-1 GHz +13 dBm (continuos) for 1-2 GHz GHz |
| +10 V |
| +10 V |
| |

3 Permanent damage may occur if these limits are exceeded.

4 Measured by keeping VG=0V.

5 Measured by keeping Vdd=5V.

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CONTROL VOLTAGE (V_g) FIG. 1

Amplifier-ON

Amplifier-OFF

Min.

1.9

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0

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Max.

0.7

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Units

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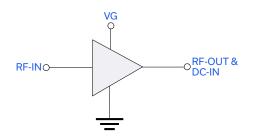
Monolithic Amplifier

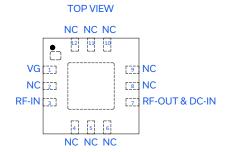
TSS-23LN+

SWITCHING SPECIFICATIONS

| Parameter | | Min. | +5V Typ. | +3V Typ. | Units | |
|--------------------------|----------------------------------|------|-------------|-------------|-------|--|
| Amplifier ON to Shutdown | OFF TIME (50% Control to 10% RF) | _ | 4.8 | 6.2 | μs | |
| | FALL TIME (90 to 10% RF) | _ | 7.4 | 3.6 | | |
| Amplifier Shutdown to ON | ON TIME (50% Control to 90% RF) | _ | 95.2 | 144.7 | | |
| | RISE TIME (10% to 90% RF) | _ | 60.0 | 200.7 | μs | |
| Control Voltage Leakage | | _ | 482.9 | 311.0 | mV | |

SIMPLIFIED SCHEMATIC AND PAD DESCRIPTION





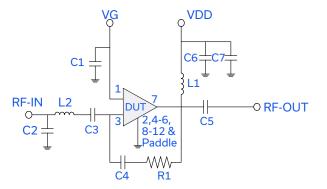
| Function | Pad Number | Description |
|------------------|--------------|------------------------------------|
| RF-IN | 3 | RF Input |
| RF-OUT and DC-IN | 7 | RF Output and DC Bias |
| GND | Paddle | Connections to ground. |
| NC | 2, 4-6, 8-12 | No connection, grounded externally |
| VG | 1 | Control voltage for shutdown (VG) |



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TSS-23LN+

CHARACTERIZATION TEST CIRCUIT / RECOMMENDED APPLICATION CIRCUIT



| Component | Size | Value | Part Number | Manufacturer |
|-----------|------|---------|--------------------|--------------|
| C1 | 0402 | 0.1uF | GRM155R71C104KA88D | Murata |
| C2 | 0402 | 1.2pF | GRM1555C1H1R2CA1D | Murata |
| C3 | 0402 | 0.1uF | GRM155R71C104KA88D | Murata |
| C4 | 0402 | 0.1uF | GRM155R71C104KA88D | Murata |
| C5 | | 1000pF | GRM1555C1H102JA01D | |
| C6 | 0402 | 10000pF | GRM155R71E103KA01D | Murata |
| C7 | 0402 | 0.1uF | GRM155R71C104KA88D | Murata |
| L1 | 0805 | 680nH | 0805LS-681XJLB | Coilcraft |
| L2 | 0402 | 1.0nH | 0402CS-1N0XJLW | Coilcraft |
| R1 | 0402 | 1.2K0hm | RK73H1ETTP1201F | Koa |

Fig 1. Block diagram of Test Circuit used for characterization. (DUT soldered on Mini-Circuits Characterization test board TB-TSS-13LN+) Gain, Return loss, Output power at 1dB compression (P1dB), output IP3 (OIP3) and noise figure measured using Agilent's N5242A PNA-X microwave network analyzer.

Conditions:

- 1. Gain and Return Loss: P_{IN} = -25dBm
- 2. Output IP3 (OIP3): Two tones, spaced 1 MHz apart, +0dBm/tone at output.
- 3. Switching Time
- RF Signal: P_{IN}=-25 dBm, fRF=500 MHz. Vdd=+3 & +5V DC, VG=Pulse signal at 1 KHz with VHIGH=+5V, VLOW=0V, 50% duty cycle.

PRODUCT MARKING



Marking may contain other features or characters for internal lot control



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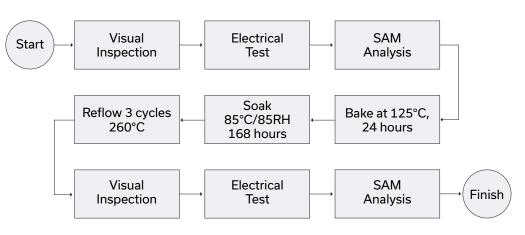
ADDITIONAL DETAILED TECHNICAL INFORMATION IS AVAILABLE ON OUR DASHBOARD. CLICK HERE

| Performance Data | Data Table Swept Graphs S-Parameter (S2P Files) Data Set (.zip file) | |
|--|--|--|
| Case Style DQ1225 Plastic package, exposed paddle lead finish: Matte-Tin | | |
| Tape & Reel Standard quantities available on reel | F66 7" reels with 20, 50, 100, 200, 500, 1K, or 2K devices | |
| Suggested Layout for PCB Design | PL-619 | |
| Evaluation Board | TB-TSS-23LN+ | |
| Environmental Ratings | ENV08T9 | |

ESD RATING

Human Body Model (HBM): Class 1A (Pass 250 V) in accordance with ANSI/ESD STM 5.1 - 2001

MSL FLOW CHART



NOTES

- A. Performance and quality attributes and conditions not expressly stated in this specification document are intended to be excluded and do not form a part of this specification document.
- B. Electrical specifications and performance data contained in this specification document are based on Mini-Circuit's applicable established test performance criteria and measurement instructions.
- C. The parts covered by this specification document are subject to Mini-Circuits standard limited warranty and terms and conditions (collectively, "Standard Terms"); Purchasers of this part are entitled to the rights and benefits contained therein. For a full statement of the standard. Terms and the exclusive rights and remedies thereunder, please visit Mini-Circuits' website at www.minicircuits.com/MCLStore/terms.jsp